



# First results on KINTEX-7 FPGA testing in mixed field radiation at CHARM facility

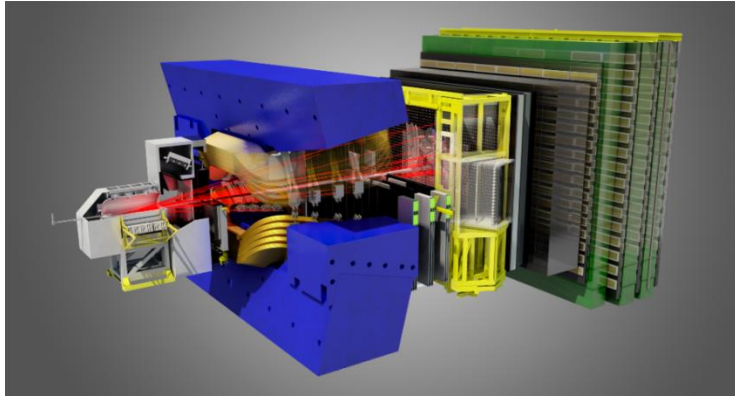
**Vlad-Mihai PLACINTA**

on behalf of the LHCb RICH PDMDB CHARM testing group

# Outline

- **Introduction**
- **Experimental Setup**
- **Preliminary Results**
- **Conclusions and Future Developments**

# Introduction



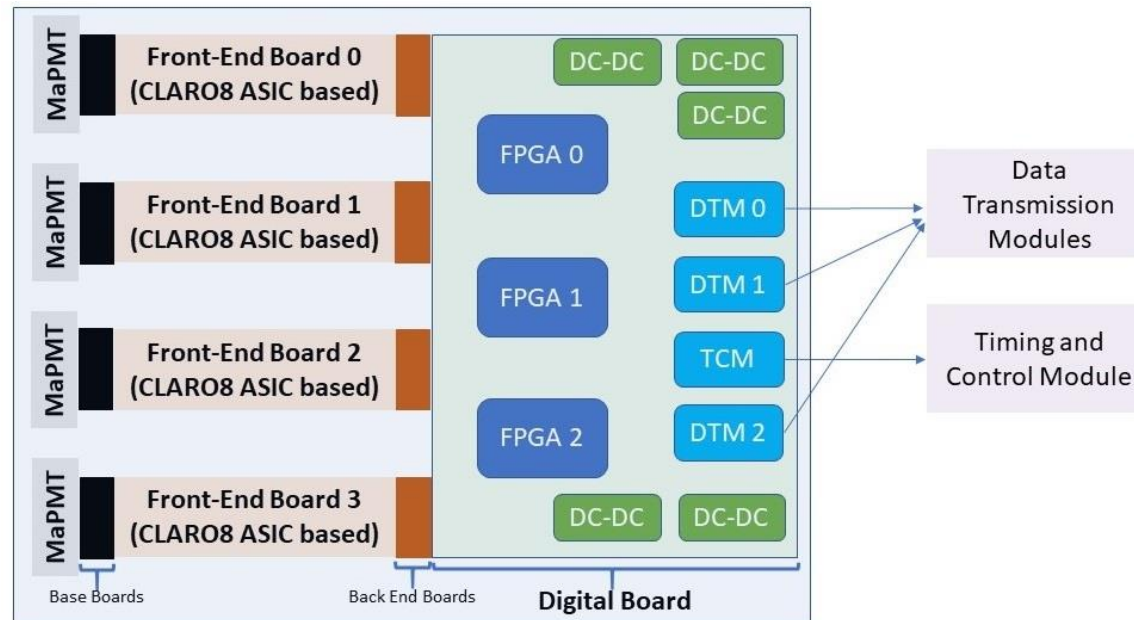
## LHCb detector

<https://lhcb-public.web.cern.ch/lhcb-public/>

Elementary Cell (typical architecture simplified)  
8 x 64 readout channels (each digital board can read  
8 MaPMTs signals)

The LHCb Collaboration, *LHCb Particle Identification Upgrade Technical Design Report*, available at: [link](#).

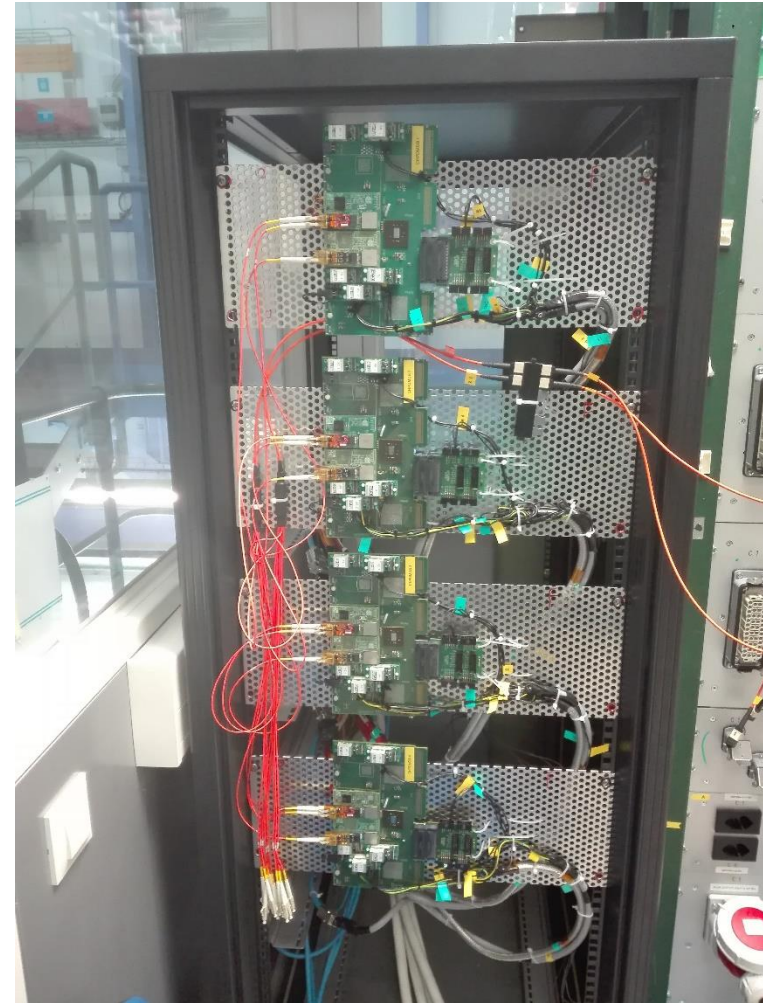
- ❖ During the second LHC long shutdown (2019-2020) the entire LHCb detector will be upgraded to operate at higher luminosity;
- ❖ The LHCb RICH sub-detectors upgraded with a 40 times increased readout rate;
- ❖ For the Digital Boards an SRAM based FPGA from Kintex-7 family has been proposed: *XC7K70T-FBG676*; (800 pieces)



# Introduction

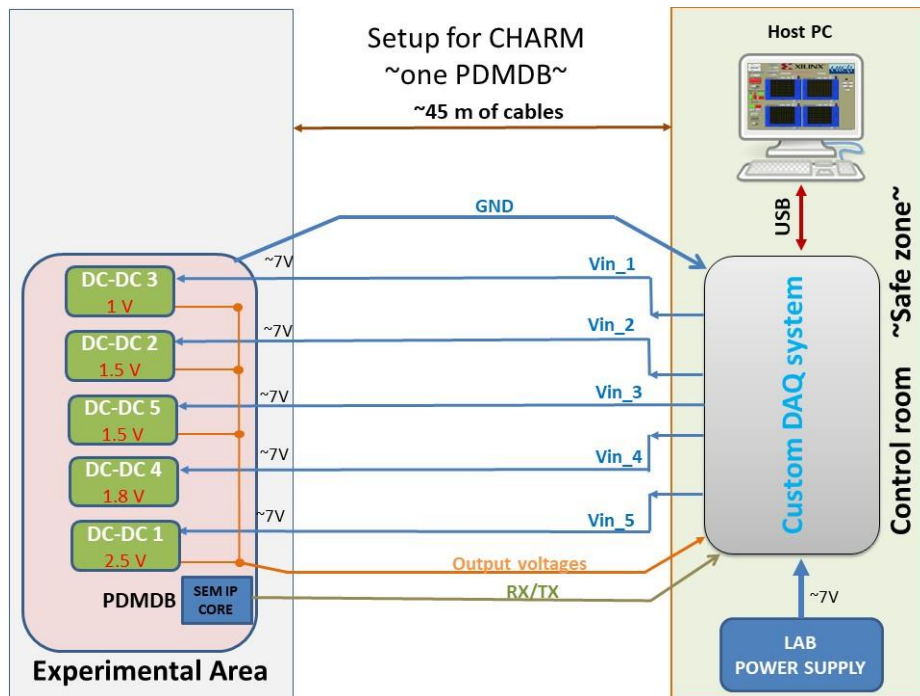
- ❖ A successful irradiation run was done last month at CERN, using the mixed field radiation facility, CHARM;
- ❖ The radiation field is generated by the interaction of a 24 GeV proton beam with a Copper target;
- ❖ We used the position 10 of the facility, further away from PS beam;
  - ❖ Softer spectra compared to LHCb-RICH;
- ❖ The radiation was performed in 2 runs, each of them of about 1 week;
- ❖ 4 boards, PDMDB type, with one FPGA KINTEX-7 each were irradiated.

<http://charm.web.cern.ch/>



# Experimental Setup

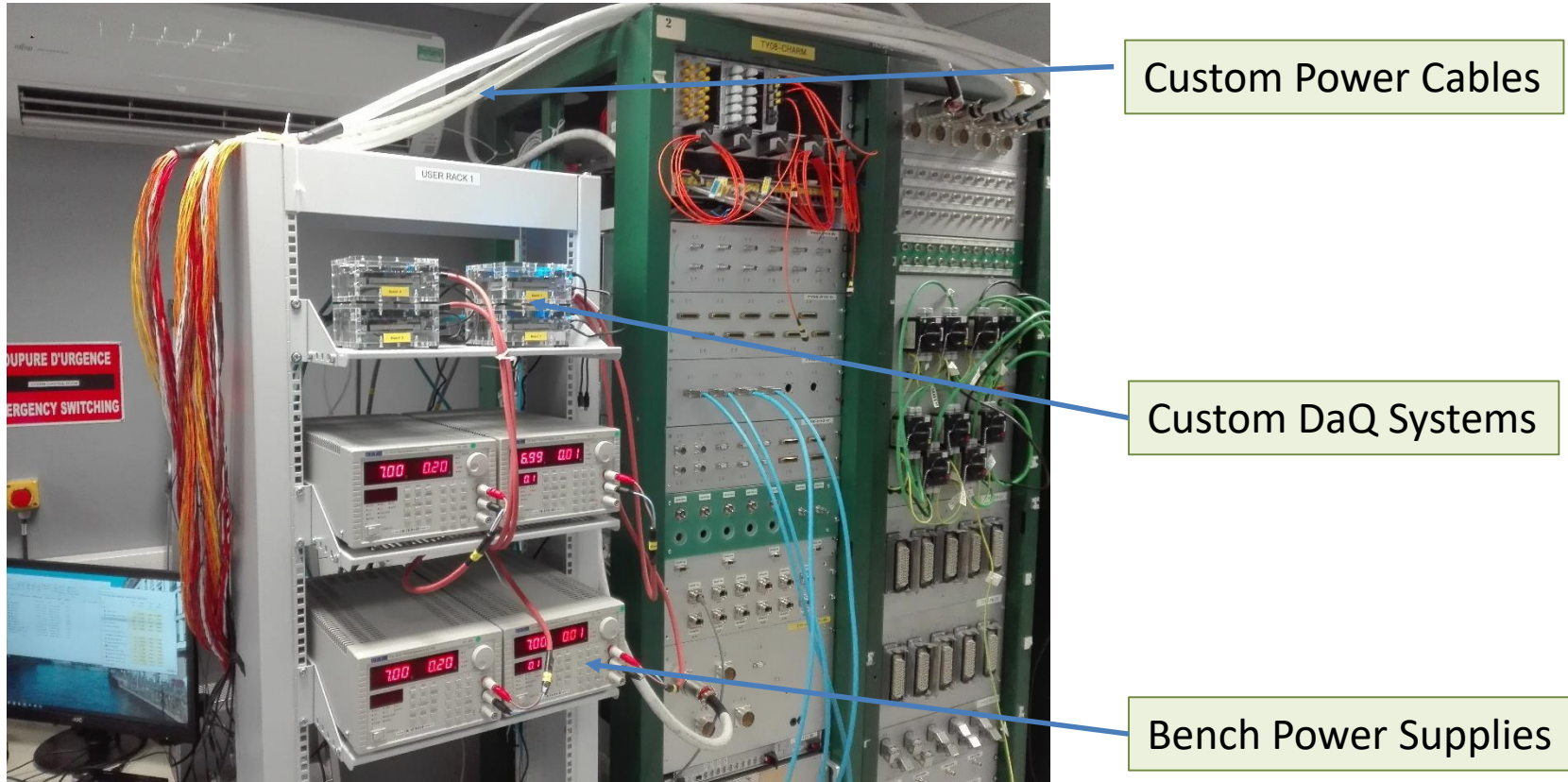
~power and electrical monitoring~



- ❖ Was implemented for each board;
- ❖ 2 of them had an UART interface used for SEM IP Core readout as CRAM mitigation;
- ❖ The power was monitored on VCCINT, VCCAUX, VCCIO and the main board supply rail;
- ❖ Boards were powered at 7 V, as will be in the Upgraded detector;
- ❖ Fail-safe functions were implemented: power cycle, reconfigurations request, alarms etc. ;
- ❖ Data was sampled at each 100-200 ms and saved in ASCII files;
- ❖ LabVIEW based GUIs.

# Experimental Setup

~power and electrical monitoring~



# Experimental Setup

~data read-out~

- ❖ Each board was configured using GBT-SCA through JTAG interface controlled by the MiniDaQ system via optical fibers;
- ❖ The MiniDaQ and the electrical monitoring systems were connected together using a DIM server (Distributed Information Management System)
  - ❖ for data exchange, power cycle request, reconfiguration request etc.;
- ❖ Logic and CRAM SEU were monitored;
- ❖ The FPGA firmware architecture was simple, with small logic usage but similar with the one proposed to be used in the future (most logic, ~90-95% , was a check routine, not to be used in RICH, and not counted in logic failures):
  - ❖ no inputs were used, a known pattern was implemented in firmware.
  - ❖ 2 versions were used one with SEM IP Core, one without.

Firmware type	Total CRAM bits	Essential bits used	SEM IP core essential bits
with SEM IP	18884576	346335 (1.8 %)	154474 (0.82%)
without SEM IP	18884576	~191861 (1 %)	

# Experimental Setup

~Sem IP Core~

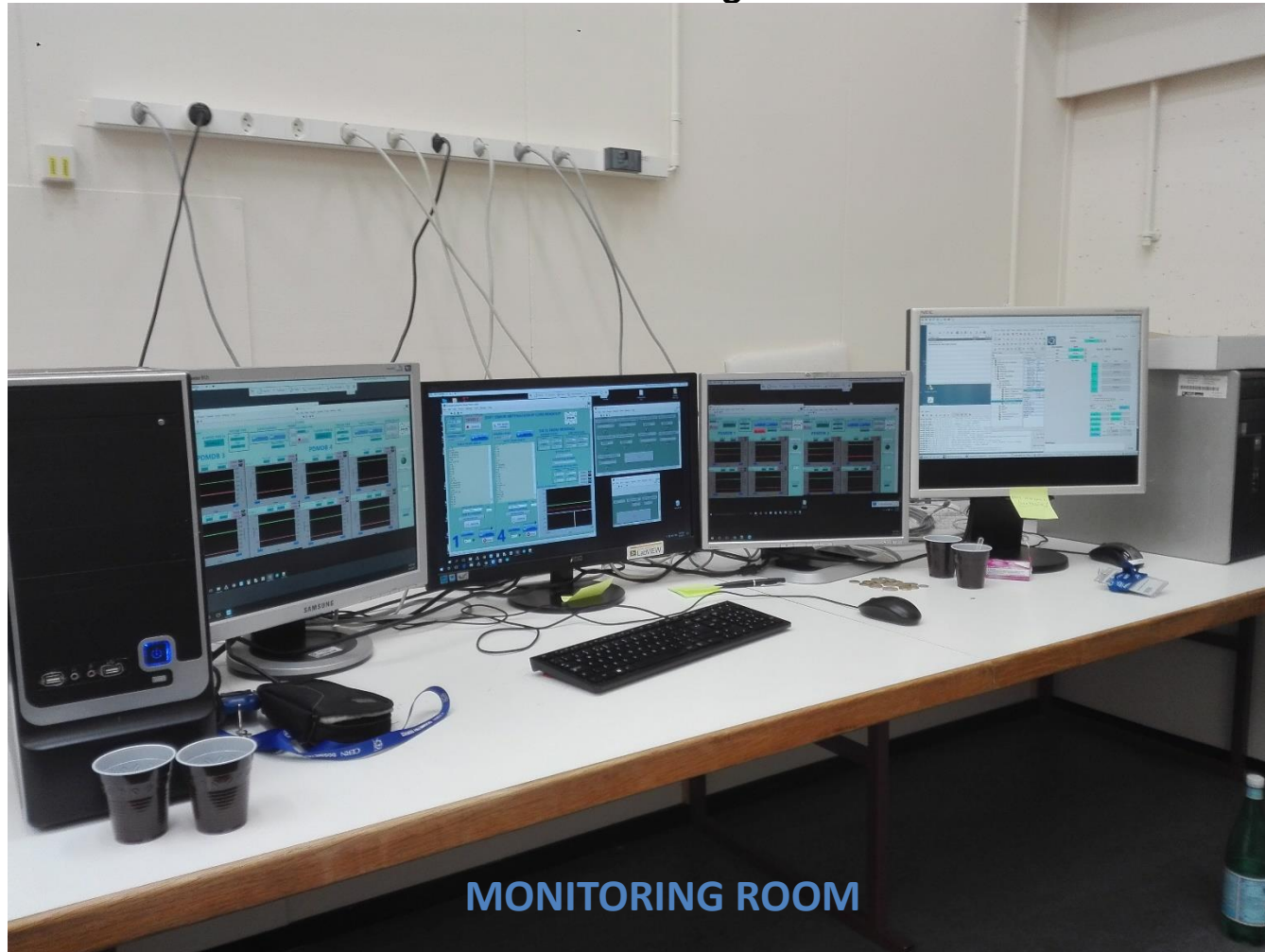
- ❖ **Soft Error Mitigation IP Core is a special IP provided free by Xilinx and used to perform SEU detection, correction and classification for the configuration memory, CRAM;**
- ❖ **The error correction is an optional feature which can be done using one of the following method:**
  - ❖ **Correction by Repair method: ECC algorithm: supports correction of configuration memory frames with single-bit errors; (one bit in each frame)**
  - ❖ **Correction by Enhanced Repair method: ECC and CRC algorithms: supports single-bit or double-bit adjacent errors;**
  - ❖ **Correction by Replace method: supports correction of configuration memory frames with arbitrary errors. (external memory needed, hence this method was not used for obvious reasons)**
- ❖ **Using the classification capability the user can determine if corrected errors have affected configuration memory in locations essential to the user design;**
- ❖ **Supports error injection: with this feature the user can inject SEU in the configuration memory which is useful for establish the critical bits ratio of he user design.**

<https://www.xilinx.com/products/intellectual-property/sem.html>

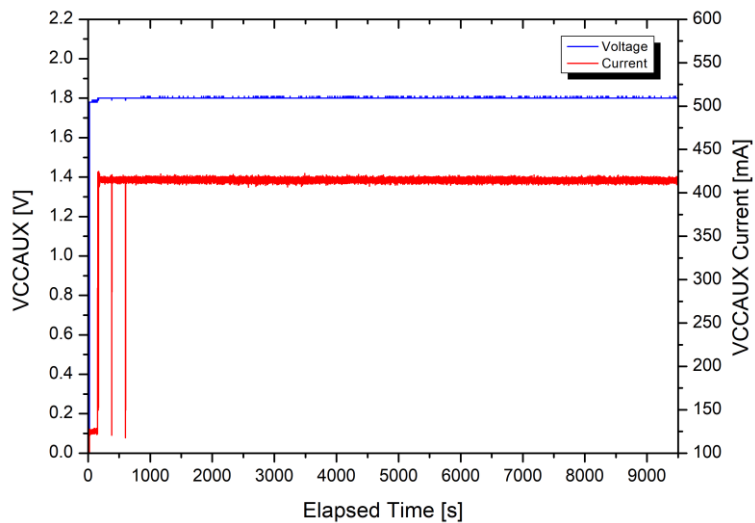
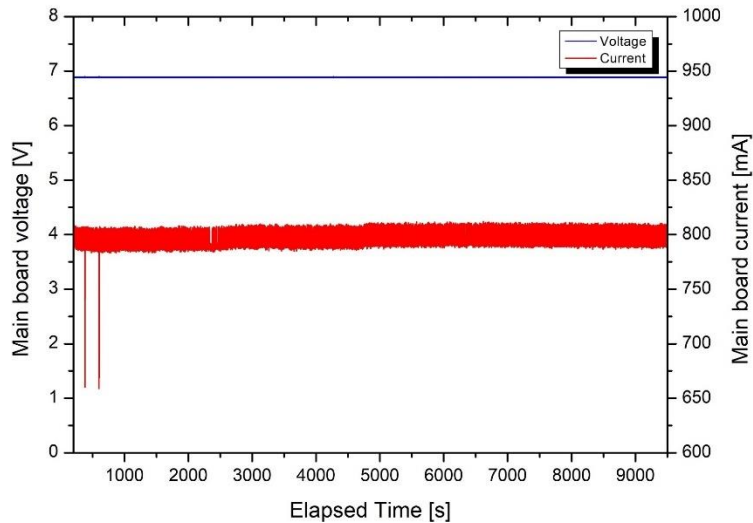


# Experimental Setup

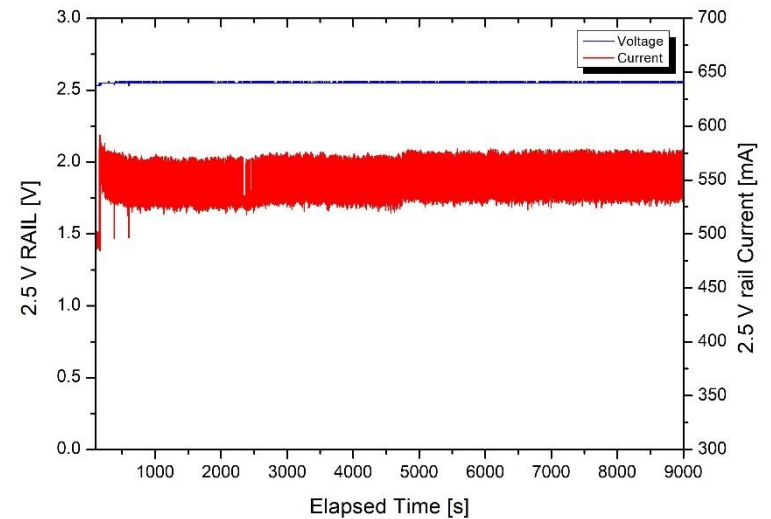
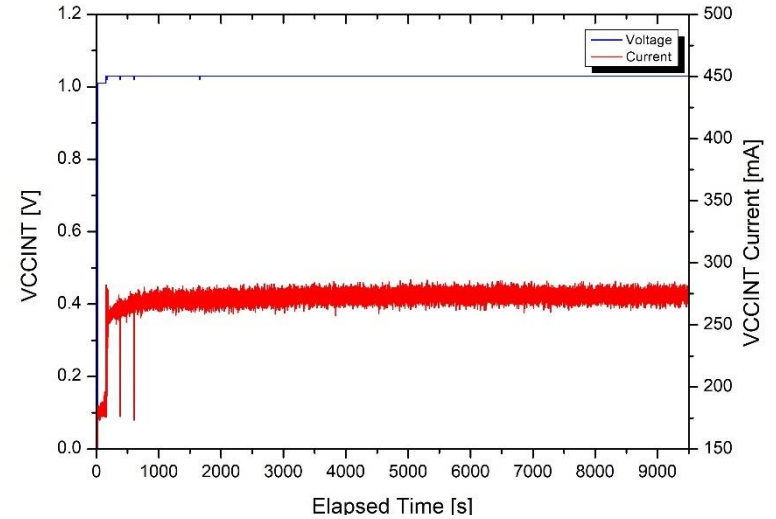
~monitoring~



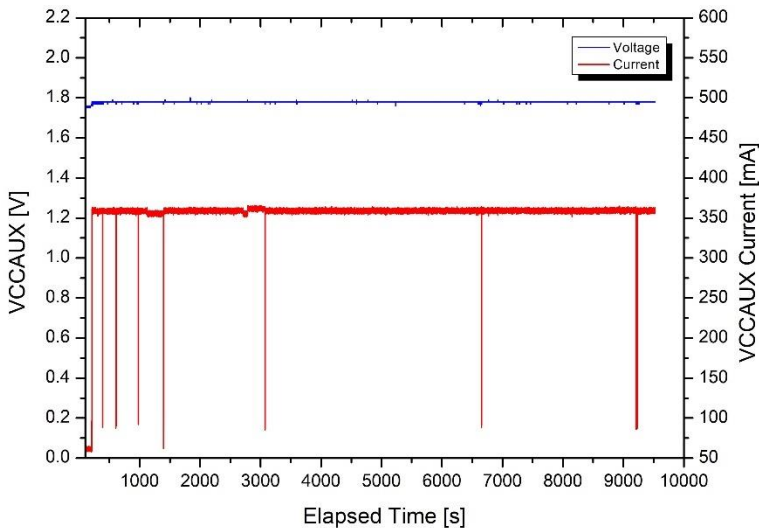
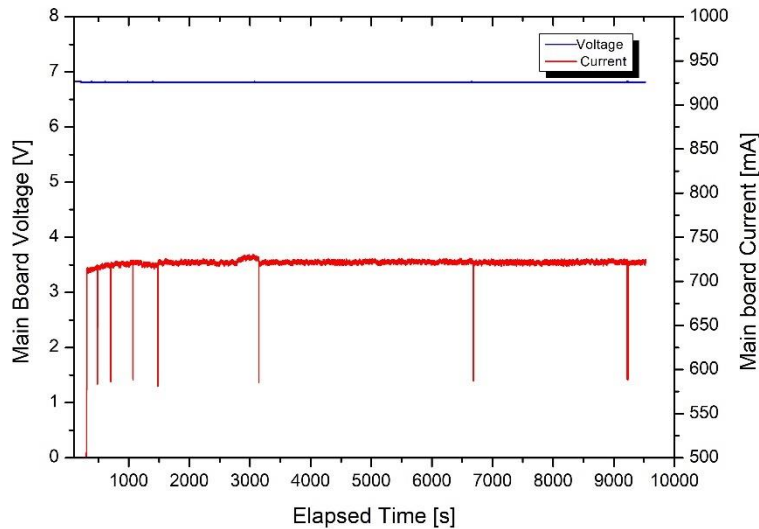
# Preliminary Results



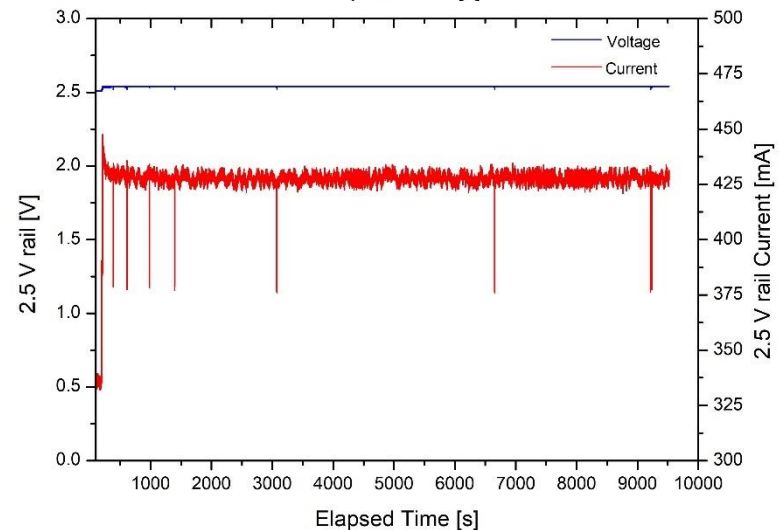
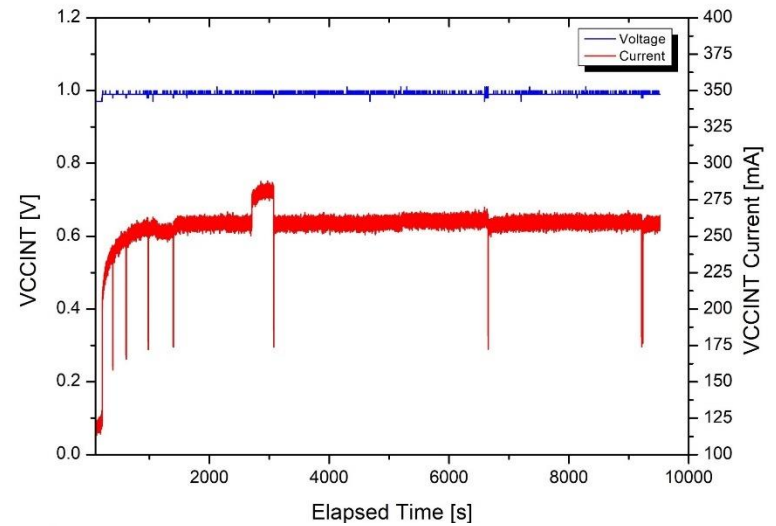
**Second PDMDB @ RUN 22  
 (without CRAM mitigation)**



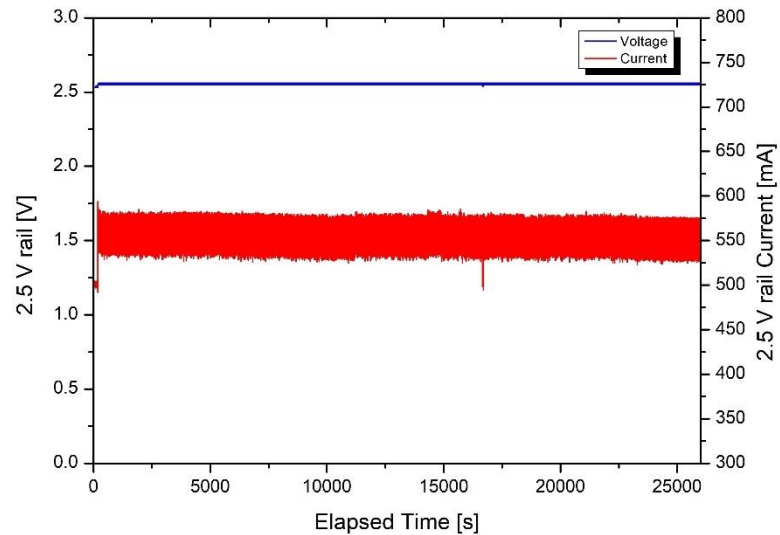
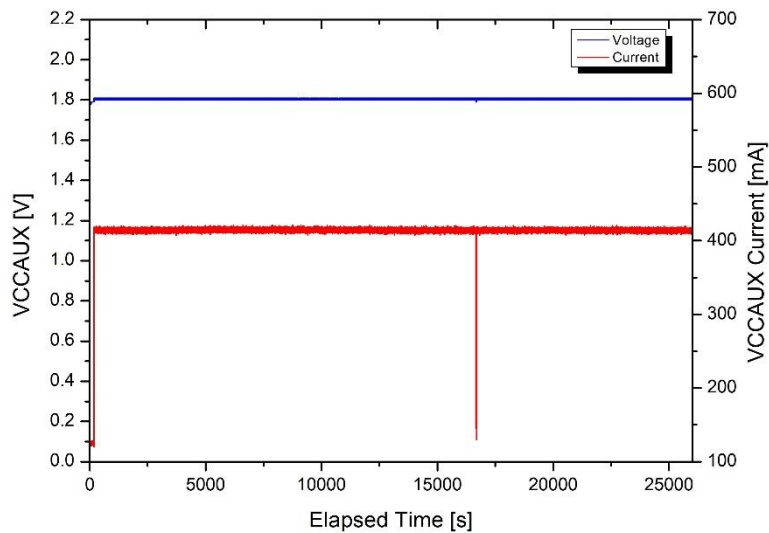
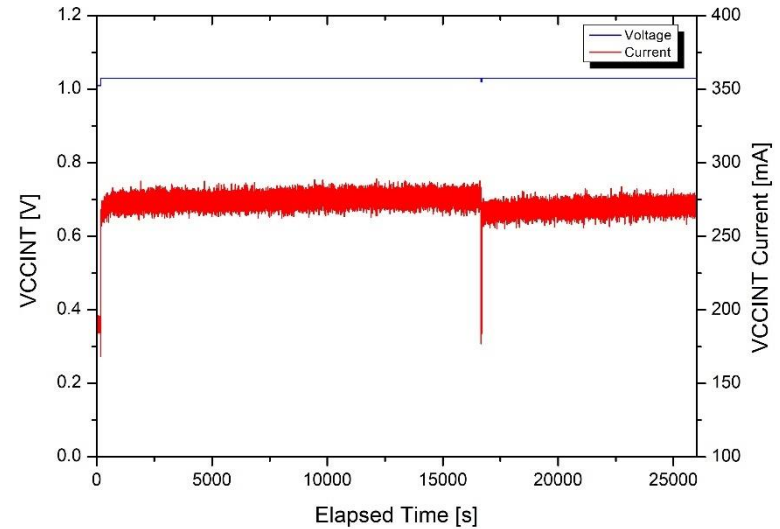
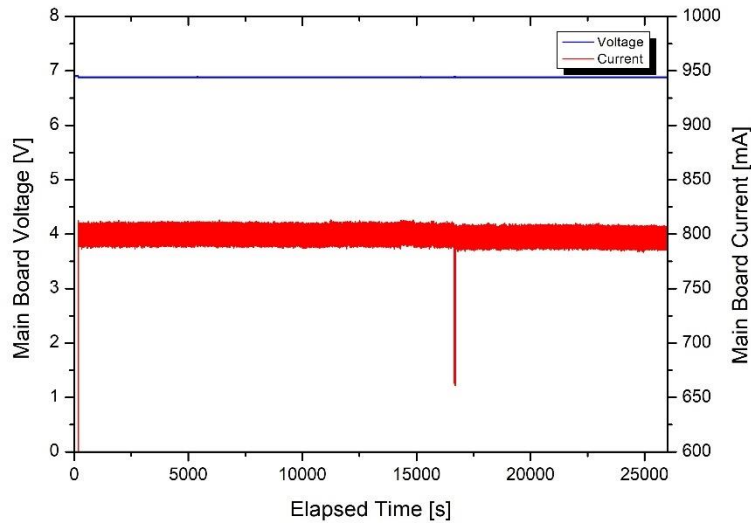
# Preliminary Results



**Forth PDMDB @ RUN 22  
(with CRAM mitigation)**



# Preliminary Results

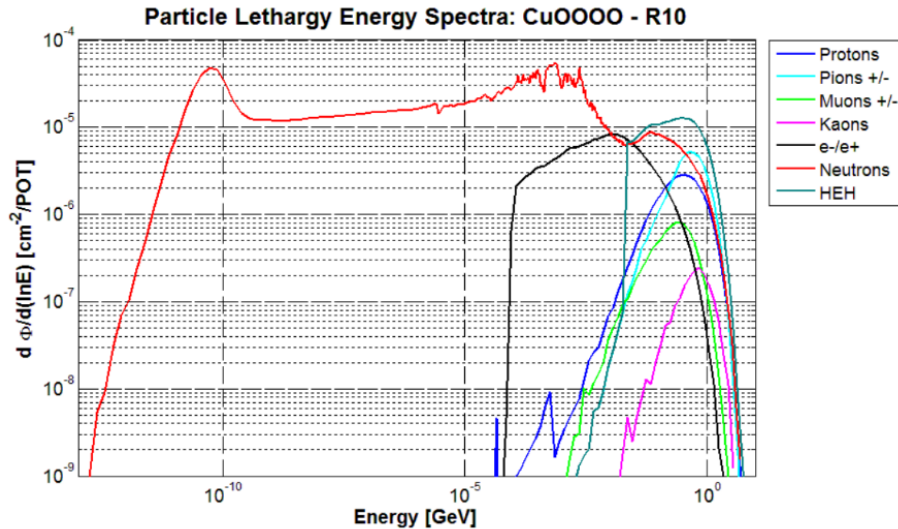


**Second PDMDB @ RUN 17  
(without CRAM mitigation)**

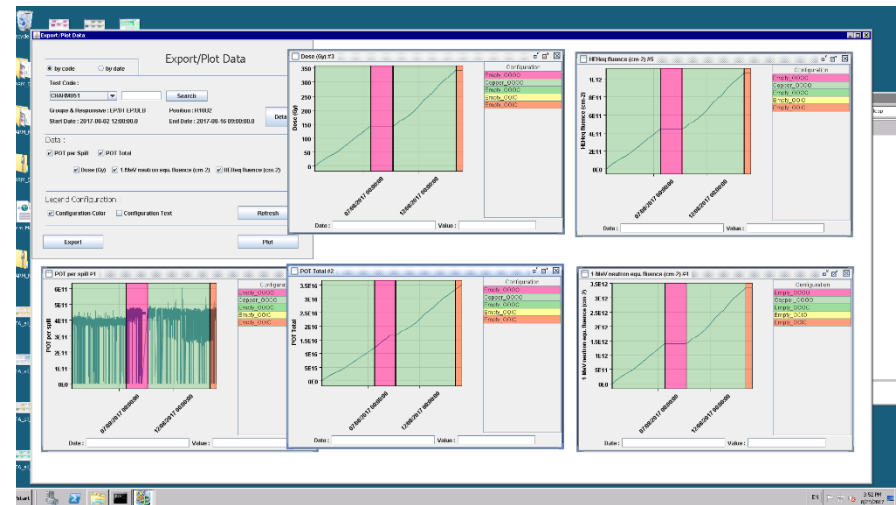
# Preliminary Results

~CHARM user dosimetry~

- ❖ 34.27 krad TID, 35 % error;
- ❖ Total HEH fluency  $10.68 \cdot 10^{11}$  with close to 70 % neutrons (> 20 MeV);
- ❖ CHARM environment similar to LHC tunnel, TID and HEH fluency order of magnitude close to expectation values for RICH-LHCb Upgrade phase at  $50 \text{ fb}^{-1}$ ;



HEH spectra in position 10



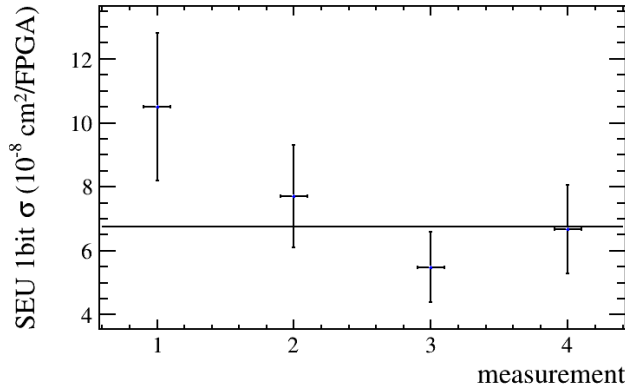
TID and HEHeq

# Preliminary Results

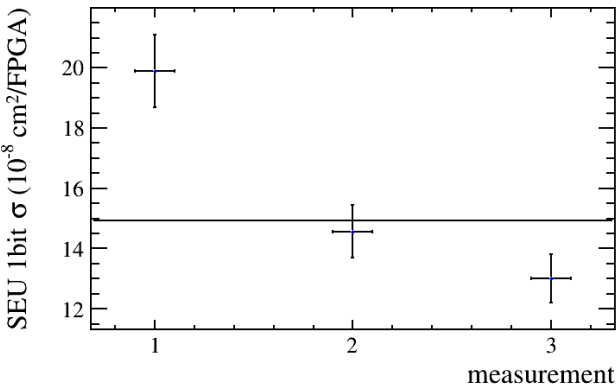
~SEU cross-section for PSI/Juelich/CHARM~

## ❖ Measurement of CRAM SEU rates through SEM IP CORE:

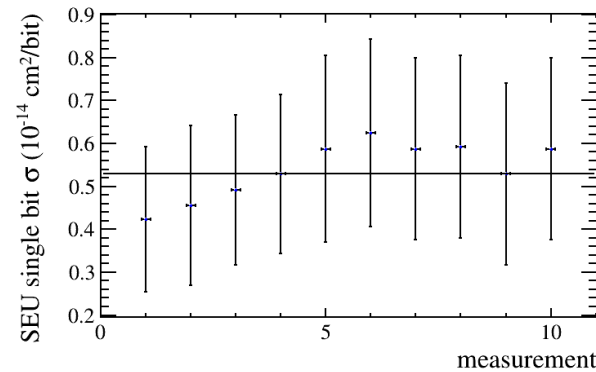
- ❖ PSI: 200 MeV protons, 500 krad per DUT, 3 DUTs;
- ❖ Juelich: 35 MeV protons, 200 krad per DUT, 3 DUTs;
- ❖ CHARM: Mixed field, close to 100 MeV average, 34 krad, 4 DUTs;



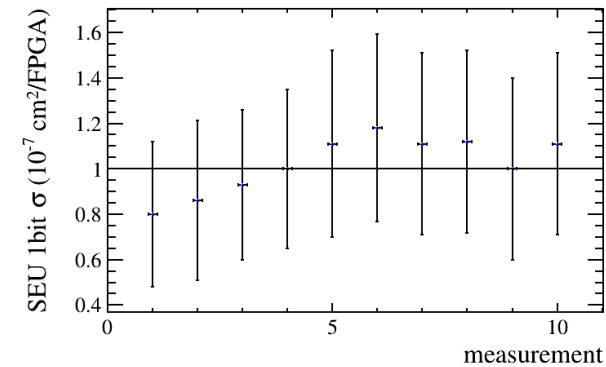
SEU cross-section PSI



SEU cross-section Juelich



SEU cross-section CHARM



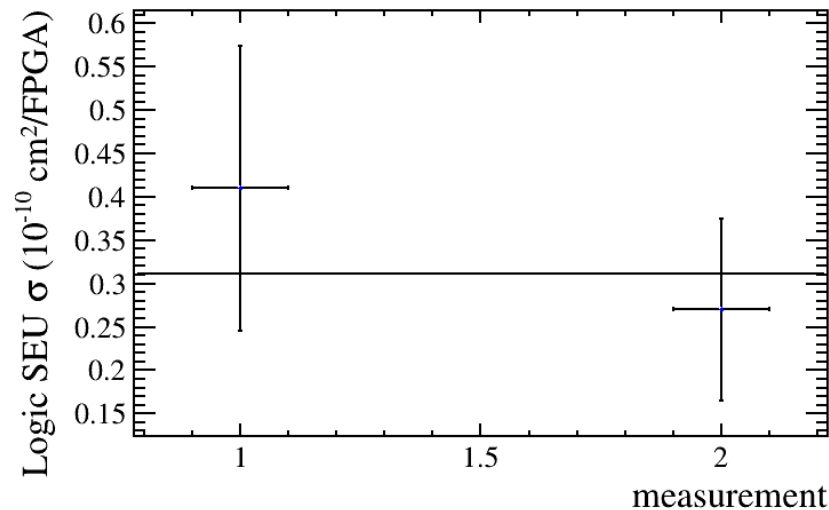
Note: This DUT has 18884576 bits of CRAM memory.

# Preliminary Results

~SEU Logic errors~

- ❖ Logic Errors are SEUs which corrupt partially or totally the User Logic on device;
- ❖ Firmware used in CHARM close to the RICH-LHCb Upgrade firmware for Digital Boards;
  - ❖ Very low number of critical CRAM bits: 6000 bits out of 18884576 bits;
- ❖ 29 logic SEUs were seen for 14.4 krad TID, with 80% DUT operational time out of all beam time, 2 DUTs;
- ❖ 38 logic SEUs were seen for 19.9 krad with 80% DUT operational time, 3 DUTs;
- ❖  $\sigma_1 = 0.41 * 10^{-10} \text{ cm}^2$  (40 % error, dominated by fluency uncertainty);
- ❖  $\sigma_2 = 0.27 * 10^{-10} \text{ cm}^2$  (39 % error, dominated by fluency uncertainty).

Logic SEU cross-section



# Preliminary Results

~Extrapolation~

- ❖ CHARM rates for few DUTs need to be extrapolated to 800 FPGA for RICH1 and RICH2 detectors;
- ❖  $50 \text{ fb}^{-1}$  integrated luminosity and  $10^{12}$  HEH fluency and 200 krad over the LHCb Upgrade phase;
- ❖ Assuming for LHCb Upgrade phase a TID/hour of 200 krad/7000 and HEH fluency/hour of  $10^{12} / 7000$ :
  - ❖ 4-5 logic SEUs in 800 FPGA during one hour;
  - ❖ About 12000 single bit SEUs in 800 FPGAs during one hour of planned LHC luminosity;
- ❖ Further uncertainty:
  - ❖ Upper values should be scaled with a safety factor of 2 to account for a harder pion spectrum in RICH versus CHARM's position 10 measurement;
  - ❖ An extra safety factor of 2-4 should be also included for uncertainty in number of critical bits of the final firmware;
  - ❖ Potential SEL events are to be discussed separately;
  - ❖ SEU in I/O banks.



# Conclusions and Future Developments

- ❖ Measurements done at CHARM on Kintex-7 FPGA have outlined a large SEU rate;
  - ❖ Cross-section of  $10^{-7} \text{ cm}^2$ ;
- ❖ The extrapolation to 800 FPGA for LHCb during Upgrade phase - HEH  $10^{12}$ :
  - ❖ Have lead to large SEU numbers and few tens of SEUs in user logic per hour;
  - ❖ it is clear that operating the 800 FPGAs for TID of 200 krad and close to LHCb primary interaction point will present challenges due to hard spectra and large incident angles;
- ❖ Though not seen in CHARM measurements, SEL are probable, even in large numbers:
  - ❖ CHARM spectrum of 100 MeV average energy with neutron “flavour” (70%) omits the hard events expected for RICH Upgrade (several GeV pions);
  - ❖ Large HEH rates above GeV and large angles make probable the SEL events seen already in ion beams for  $15 \text{ MeV} \cdot \text{cm}^2 / \text{mg}$  (micro-SEL) and  $32\text{-}35 \text{ MeV} \cdot \text{cm}^2 / \text{mg}$  thresholds.